### SPECIFICATIONS

### ABSOLUTE MAXIMUM RATINGS at Ta = $25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		50	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	۱ <sub>D</sub>		0.1	А
Drain Current (Pulse)	I <sub>DP</sub>	PW $\leq$ 10 $\mu$ s, duty cycle $\leq$ 1%	0.4	А
Allowable Power Dissipation	PD		0.15	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

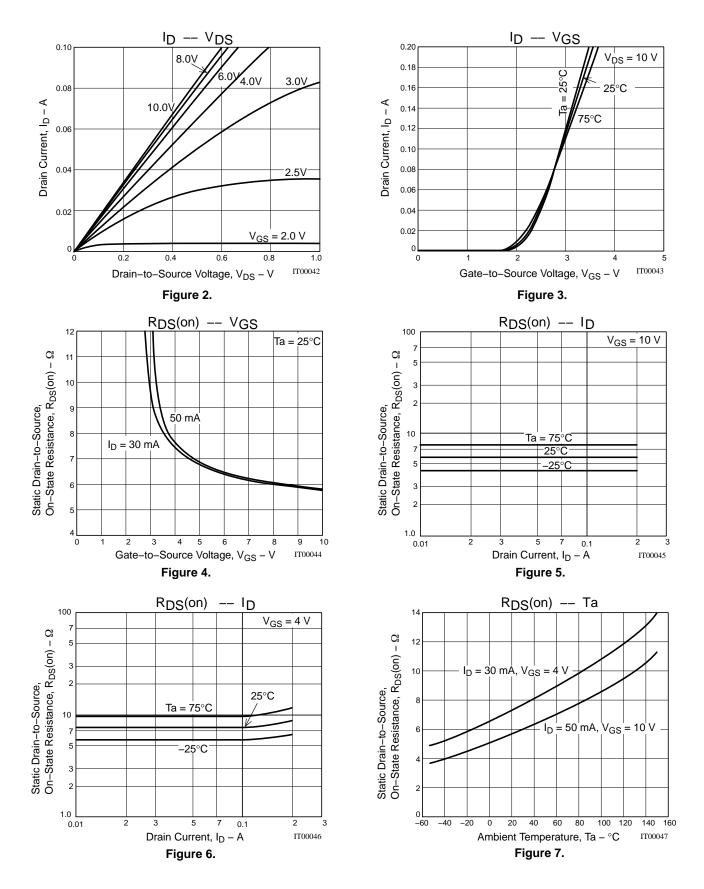
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **ELECTRICAL CHARACTERISTICS** at Ta = 25°C

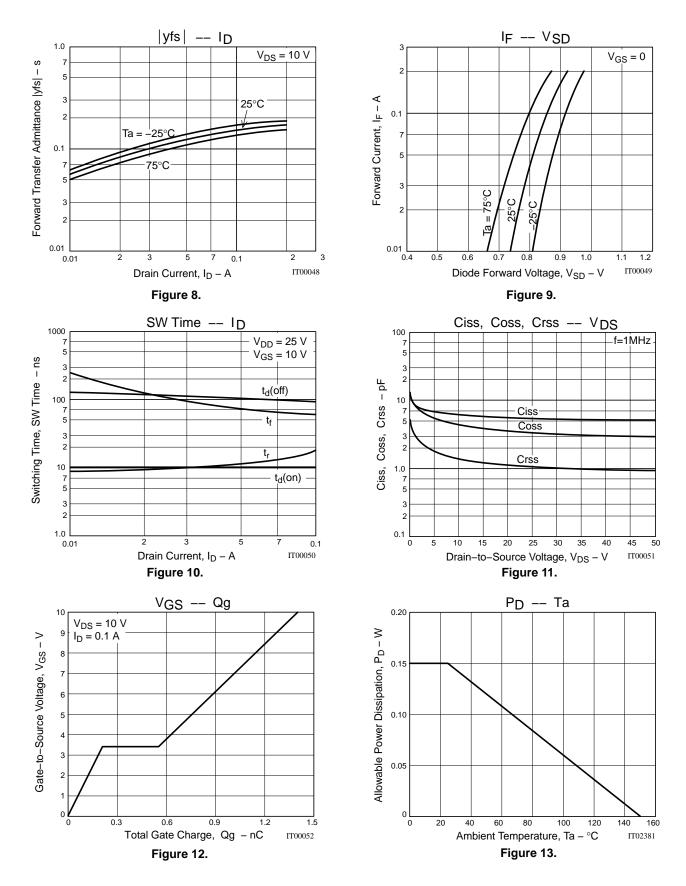
			Ratings			
Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$I_{D} = 1 \text{ mA}, V_{GS} = 0$	50			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0$			1	μΑ
Gate-to-Sourse Leakage Current	I <sub>GSS</sub>	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = -100 \mu\text{A}$	<sub>DS</sub> = 10 V, I <sub>D</sub> = -100 μA 1		2.4	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 50 mA	85	120		mS
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> = 50 mA, V <sub>GS</sub> = 10 V		5.8	7.5	Ω
	R <sub>DS</sub> (on)2	I <sub>D</sub> = 30 mA, V <sub>GS</sub> = 4 V		7.5	10.5	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = 10 V, f = 1 MHz	<sub>S</sub> = 10 V, f = 1 MHz 6.			pF
Output Capacitance	Coss	V <sub>DS</sub> = 10 V, f = 1 MHz		4.4		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> = 10 V, f = 1 MHz		1.5		pF
Turn-ON Delay Time	t <sub>d</sub> (on)	See specified Test Circuit	10			ns
Rise Time	t <sub>r</sub>	See specified Test Circuit	cuit 11			ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit	pecified Test Circuit 105			ns
Fall Time	t <sub>f</sub>	See specified Test Circuit 75			ns	
Total Gate Charge	Qg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA 1.40			nC	
Gate Source Charge	Qgs	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA 0.21			nC	
Gate Drain Charge	Qgd	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 mA 0.34			nC	
Diode Forward Voltage	VSD	I <sub>S</sub> = 100 mA, V <sub>GS</sub> = 0 0.85 1		1.2	V	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### **TYPICAL CHARACTERISTICS**

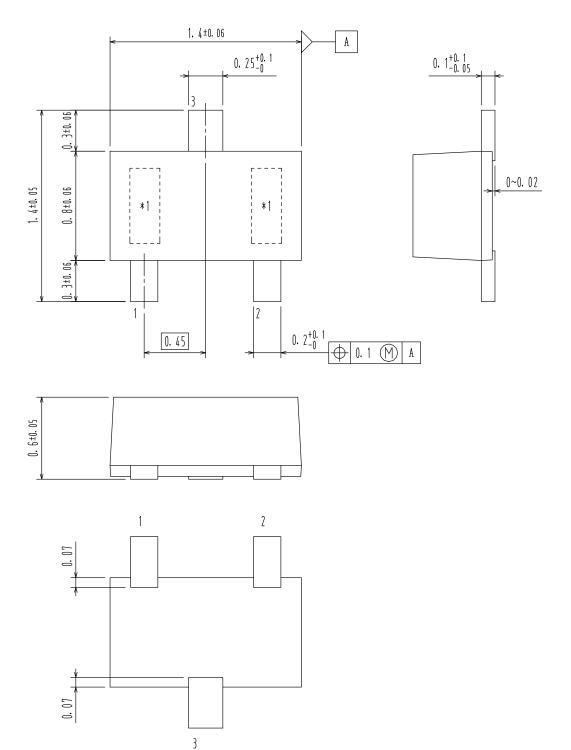


## **TYPICAL CHARACTERISTICS**



### PACKAGE DIMENSIONS

SOT-623 / SSFP CASE 631AC ISSUE O



#### **ORDERING INFORMATION**

Device	Marking	Package	Shipping <sup>†</sup>
5HN01SS-TL-E / 5HN01SS-TL-H	YC	SOT–623 / SSFP (Pb–Free / Halogen Free)	8,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

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